

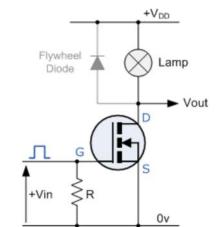
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In this circuit arrangement an Enhancement-mode N-channel MOSFET is being used to switch a simple lamp "ON" and "OFF" (could also be an LED). The gate input voltage  $V_{GS}$  is taken to an appropriate positive voltage level to turn the device and the lamp either fully "ON", ( $V_{GS}$  = +ve) or a zero voltage level to turn the device fully "OFF", ( $V_{GS}$  = 0).

If the resistive load of the lamp was to be replaced by an inductive load such as a coil or solenoid, a "Flywheel" diode would be required in parallel with the load to protect the MOSFET from any back-emf. Ads by Google

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Above shows a very simple circuit for switching a resistive load such as a lamp or LED. But when using power MOSFET's to switch either inductive or capacitive loads some form of protection is required to prevent the MOSFET device from becoming damaged. Driving an inductive load has the opposite effect from driving a capacitive load. For example, a capacitor without an electrical charge is a short circuit, resulting in a high "inrush" of current and when we remove the voltage from an inductive load we have a large reverse voltage build up as the magnetic field collapses, resulting in an induced back-emf in the windings of the inductor.

For the power MOSFET to operate as an analogue switching device, it needs to be switched between its "Cut-off Region" where  $V_{GS} = 0$  and its "Saturation Region" where  $V_{GS(on)} = +ve$ . The power dissipated in the MOSFET (P<sub>D</sub>) depends upon the current flowing through the channel I<sub>D</sub> at saturation and also the "ON-resistance" of the channel given as  $R_{DS(on)}$ . For example.

## Example No1

Lets assume that the lamp is rated at 6v, 24W and is fully "ON" and the standard MOSFET has a channel "ON-resistance" ( $R_{DS(on)}$ ) value of 0.10hms. Calculate the power dissipated in the MOSFET switch.

The current flowing through the lamp is calculated as:

$$P = V \times I$$
, therefore,  $I_D = \frac{P}{V} = \frac{24}{6} = 4 \text{ amps}$ 

Then the power dissipated in the MOSFET will be given as:

$$P_{D} = I_{D}^{2} \times R_{DS}$$
, therefore,  $P_{D} = 4^{2} \times 0.1 = 1.6$  watts

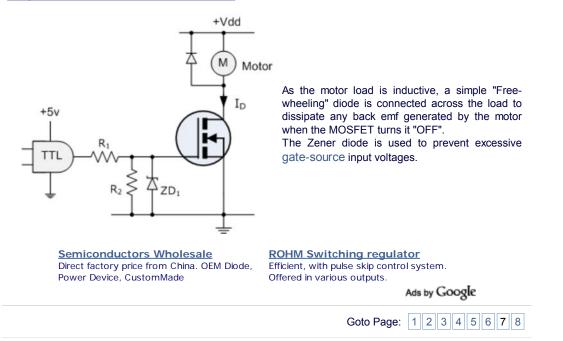
You may think, well so what!, but when using the MOSFET as a switch to control DC motors or high inrush current devices the "ON" channel resistance ( $R_{DS(on)}$ ) is very important. For example, MOSFET's that control DC motors, are subjected to a high in-rush current as the motor first begins to rotate. Then a high  $R_{DS(on)}$  channel resistance value would simply result in large amounts of power being dissipated within the MOSFET itself resulting in an excessive temperature rise, and which in turn could result in the MOSFET

becoming very hot and damaged due to a thermal overload. But a low  $R_{DS(on)}$  value on the other hand is also desirable to help reduce the effective saturation voltage ( $V_{DS(sat)} = I_D \times R_{DS(on)}$ ) across the MOSFET. When using MOSFET's or any type of Field Effect Transistor for that matter as a switching device, it is always advisable to select ones that have a very low  $R_{DS(on)}$  value or at least mount them onto a suitable heatsink to help reduce any thermal runaway and damage.

## **Power MOSFET Motor Control**

Because of the extremely high input or Gate resistance that the MOSFET has, its very fast switching speeds and the ease at which they can be driven makes them ideal to interface with op-amps or standard logic gates. However, care must be taken to ensure that the gate-source input voltage is correctly chosen because when using the **MOSFET as a switch** the device must obtain a low  $R_{DS(on)}$  channel resistance in proportion to this input gate voltage. For example, do not apply a 12v signal if a 5v signal voltage is required. Power MOSFET's can be used to control the movement of DC motors or brushless stepper motors directly from computer logic or Pulse-width Modulation (PWM) type controllers. As a DC motor offers high starting torque and which is also proportional to the armature current, MOSFET switches along with a PWM can be used as a very good speed controller that would provide smooth and quiet motor operation.

## Simple Power MOSFET Motor Controller



External Links about using the MOSFET as a Switch MOSFET Switch Drivers - Good Tutorial Explaining how to use the MOSFET as a Switch. Purdue University IGFET's - pdf File Explaining how to use and Connect IGFET's. Socratic Electronics Using a MOSFET as a Switch - Tutorial about using a MOSFET as a Switch. Burning Software MOSFET's and their Applications - Introduction to Power MOSFET's and their Applications. National Semiconductor Link to us : http://www.electronics-tutorials.ws/transistor/tran\_7.html

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